

# CNZ1179

## Photo Interrupter

For contactless SW, object detection

### Overview

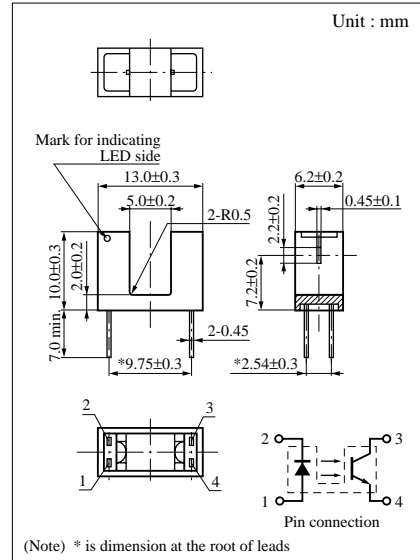
CNZ1179 is a photocoupler in which a high efficiency GaAs infrared light emitting diode is used as the light emitting element, and a high sensitivity phototransistor is used as the light detecting element. The two elements are arranged so as to face each other, and objects passing between them are detected.

### Features

- Highly precise position detection : 0.3 mm
- Wide gap between emitting and detecting elements, suitable for thick plate detection
- Fast response :  $t_r, t_f = 6 \mu s$  (typ.)
- Small output current variation against change in temperature

### Absolute Maximum Ratings (Ta = 25°C)

Parameter		Symbol	Ratings	Unit
Input (Light emitting diode)	Reverse voltage (DC)	$V_R$	3	V
	Forward current (DC)	$I_F$	50	mA
	Power dissipation	$P_D^{*1}$	75	mW
Output (Photo transistor)	Collector current	$I_C$	20	mA
	Collector to emitter voltage	$V_{CEO}$	30	V
	Emitter to collector voltage	$V_{ECO}$	5	V
	Collector power dissipation	$P_C^{*2}$	100	mW
Temperature	Operating ambient temperature	$T_{opr}$	-25 to +85	°C
	Storage temperature	$T_{stg}$	-30 to +100	°C



\*1 Input power derating ratio is 1.0 mW/°C at Ta ≥ 25°C.

\*2 Output power derating ratio is 1.33 mW/°C at Ta ≥ 25°C.

### Electrical Characteristics (Ta = 25°C)

Parameter		Symbol	Conditions	min	typ	max	Unit
Input characteristics	Forward voltage (DC)	$V_F$	$I_F = 50mA$		1.2	1.5	V
	Reverse current (DC)	$I_R$	$V_R = 3V$			10	$\mu A$
Output characteristics	Collector cutoff current	$I_{CEO}$	$V_{CE} = 10V$			200	nA
	Collector to emitter capacitance	$C_C$	$V_{CE} = 10V, f = 1MHz$		5		pF
Transfer characteristics	Collector current	$I_C$	$V_{CE} = 10V, I_F = 20mA, R_L = 100\Omega$	0.3			mA
	Response time	$t_r, t_f^{*}$	$V_{CC} = 10V, I_C = 1mA, R_L = 100\Omega$		6		$\mu s$
	Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_F = 50mA, I_C = 0.1mA$			0.3	V

\* Switching time measurement circuit

